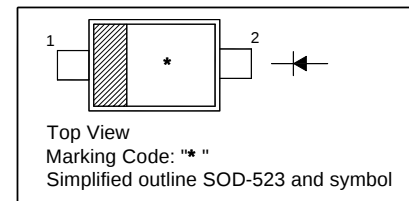


Silicon Epitaxial Planar Schottky Barrier Diode

for high speed switching application

PINNING

PIN	DESCRIPTION
1	Cathode
2	Anode

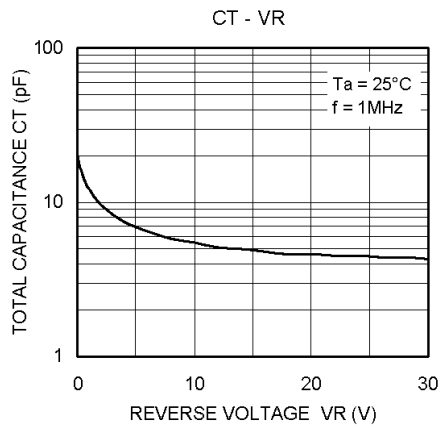
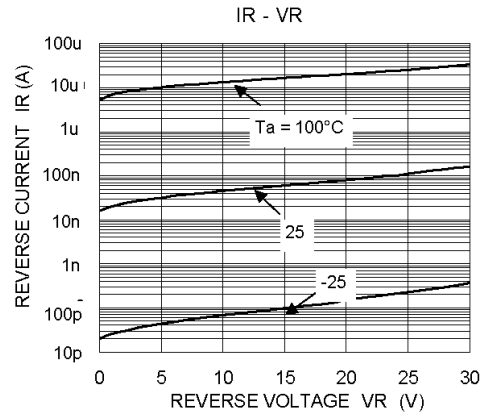
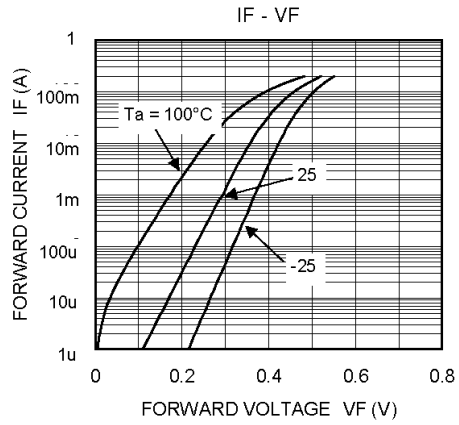


Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Peak Reverse Voltage	V_{RM}	35	V
Reverse Voltage	V_R	30	V
Average Forward Current	$I_{F(AV)}$	200	mA
Peak Forward Current	I_{FM}	300	mA
Power Dissipation	P_{tot}	150	mW
Surge Current (10 ms)	I_{FSM}	1	A
Junction Temperature	T_j	125	$^\circ\text{C}$
Operating Temperature Range	T_{opr}	- 40 to + 100	$^\circ\text{C}$
Storage Temperature	T_{stg}	- 55 to + 125	$^\circ\text{C}$

Characteristics at $T_a = 25^\circ\text{C}$

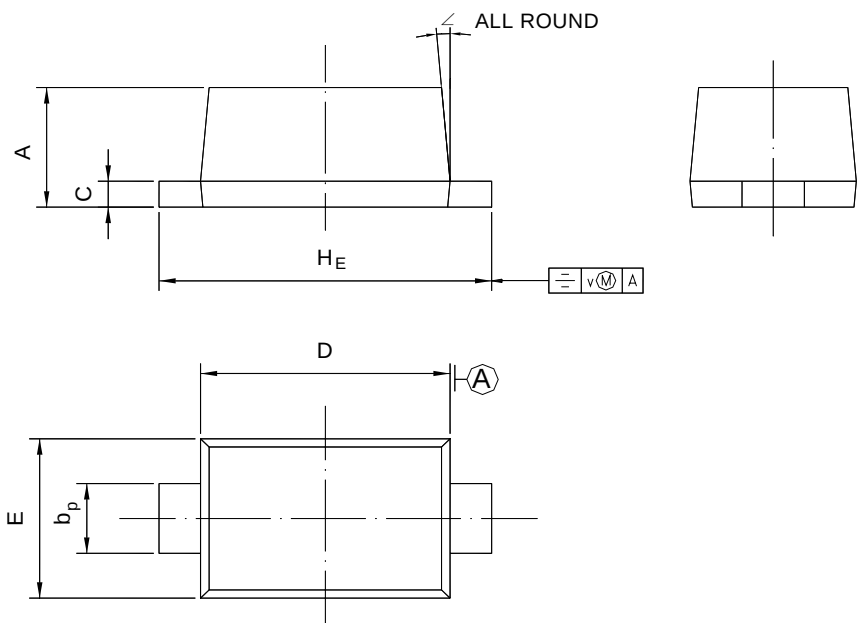
Parameter	Symbol	Typ.	Max.	Unit
Forward Voltage at $I_F = 200\text{ mA}$	V_F	-	0.6	V
Reverse Current at $V_R = 30\text{ V}$	I_R	-	5	μA
Total Capacitance at $V_R = 0\text{ V}$, $f = 1\text{ MHz}$	C_T	20	-	pF



PACKAGE OUTLINE

Plastic surface mounted package; 2 leads

SOD-523



UNIT	A	b _p	C	D	E	H _E	V	∠
mm	0.70 0.60	0.4 0.3	0.135 0.100	1.25 1.15	0.85 0.75	1.7 1.5	0.1	5°